

## ABSTRACT OF THE DISCLOSURE

The present invention relates to a film forming method of forming an interlayer insulating film having a low dielectric constant for covering wiring. The insulating film covering wiring is formed on a substrate by converting into a plasma and reacting a film forming gas including a component selected from the group consisting of alkoxy compounds having Si-H bonds and siloxanes having Si-H bonds and an oxygen-containing gas selected from a group consisting of O<sub>2</sub>, N<sub>2</sub>O, NO<sub>2</sub>, CO, CO<sub>2</sub>, and H<sub>2</sub>O.